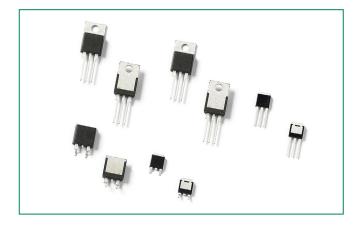


Sxx08xSx & Sxx08x Series



RoHS



Agency Approval

Agency	Agency File Number
71 °	L Package: E71639

Main Features

Symbol	Value	Unit
I _{T(RMS)}	8	А
V_{DRM}/V_{RRM}	400 to 1000	V
l _{GT}	0.2 to 15	mA

Additional Information







Samples

Description

This Sxx08x SCR series is ideal for uni-directional switch applications such as phase control, heating, motor speed controls, converters/rectifiers and capacitive discharge ignitions.

These SCRs have a low gate current trigger level of 0.2 to 15 mA at approximately 1.5V, with a sensitive version of this series having a gate trigger current less than $500\mu A$. The sensitive gate SCR version is easily triggered by sense coils, proximity switches, and microprocessors.

Features & Benefits

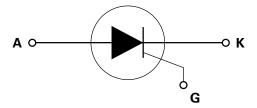
- Halogen Free and RoHS compliant
- Glass passivated junctions
- Voltage capability up to 1000 V
- Surge capability up to 100 A at 60 Hz half cycle
- L Package is UL recognized for 2500Vrms

Applications

Typical applications are capacitive discharge systems for strobe lights, nailers, staplers and gas engine ignition. Also AC control & rectification for power tools, home/brown goods, white goods appliances and 2-wheeler rectifier/battery regulators.

Internally constructed isolated packages are offered for ease of heat sinking with highest isolation voltage.

Schematic Symbol



Absolute Maximum Ratings —	Sensitive SCRs
----------------------------	----------------

Symbol	Parameter	Test Cond	litions	Value	Unit
		Sxx08LSy	$T_c = 80$ °C		
I _{T(RMS)}	RMS on-state current	Sxx08RSy/Sxx08NSy Sxx08DSy Sxx08VSy	T _c = 95°C	8	А
		Sxx08LSy	$T_c = 80^{\circ}C$		
I _{T(AV)}	Average on-state current	Sxx08RSy/Sxx08NSy Sxx08DSy Sxx08VSy	T _c = 95°C	5.1	А
	Peak non-repetitive surge current	single half cycle; $f = 50Hz$; T_J (initial) = 25°C		83	А
^I TSM	r eak norriepetitive surge current	single half cycle; $f = 60Hz$; T_J (initial) = 25°C		100	
l²t	I²t Value for fusing	$t_p = 8.3$	ms	41	A²s
di/dt	Critical rate of rise of on-state current	f = 60 Hz ; T	_ = 110°C	70	A/µs
I _{GTM}	Peak gate current	$T_{J} = 110$	0°C	1.6	А
P _{G(AV)}	Average gate power dissipation $T_J = 110$ °C		D°C	0.4	W
T _{stg}	Storage temperature range			-40 to 150	°C
T _J	Operating junction temperature range			-40 to 110	°C

Note: xx = voltage, y = sensitivity

Absolute Maximum Ratings — Standard SCRs

Symbol	Parameter	Test Condi	tions	Value	Unit
		Sxx08L	T _C = 100°C		
I _{T(RMS)}	RMS on-state current	Sxx08R/Sxx08N Sxx08D Sxx08V	T _C = 110°C	8	А
		Sxx08L	T _C = 100°C		
I _{T(AV)}	Average on-state current	Sxx08R/Sxx08N Sxx08D Sxx08V	T _C = 110°C	5.1	А
	Peak non-repetitive surge current	single half cycle; $f = 50Hz$; T_J (initial) = 25°C		83	А
I _{TSM}	i eak norriepetitive surge current	single half cycle; f = 60Hz; T _J (initial) = 25°C		100	7
l²t	I²t Value for fusing	$t_p = 8.3 r$	ns	41	A ² s
di/dt	Critical rate-of-rise of on-state current	$f = 60 \text{ Hz T}_{J} =$: 125°C	100	A/µs
I _{GM}	Peak gate current	T _J = 125	°C	2	А
P _{G(AV)}	Average gate power dissipation	T _J = 125°C		0.5	W
T _{stg}	Storage temperature range			-40 to 150	°C
T _J	Operating junction temperature range			-40 to 125	°C

Note: xx = voltage



Electrical Characteristics (T_J = 25°C, unless otherwise specified) – Sensitive SCRs

Symbol	Symbol Test Conditions		Value				- Unit	
Syllibol			Sxx08xS1	Sxx08xS2	Sxx08xS3	Sxx08x4	Offic	
I _{GT}	$V_D = 6V R_L = 100 \Omega$	MAX.	50	200	500	100	μΑ	
V _{GT}	$V_D = 6V R_L = 100 \Omega$	MAX.		0	.8		V	
dv/dt	$V_D = V_{DRM}$; $R_{GK} = 1k\Omega$; $T_J = 110$ °C	TYP.	2 8			V/µs		
$V_{\rm GD}$	$V_D = V_{DRM} R_L = 3.3 \text{ k}\Omega T_J = 110^{\circ}\text{C}$	MIN.	0.2			V		
V_{GRM}	$I_{GR} = 10\mu A$	MIN.	6		V			
I _H	$I_{T} = 20$ mA (initial)	MAX.	4	6	8	5	mA	
t _q	$I_T = 2A$; $t_p = 50\mu s$; $dv/dt = 5V/\mu s$; $di/dt = -30A/\mu s$	MAX.	75	50	45	60	μs	
t _{gt}	$I_{G} = 2 \times I_{GT}$ PW = 15 μ s $I_{T} = 12A$	TYP.	3	4	5	4	μs	

Note: xx = voltage x = package

Electrical Characteristics (T₁ = 25°C, unless otherwise specified) – Standard SCRs

Symbol	Test Conditions			Value	Unit	
Syllibol	lest Conditions			Sxx08x	Onit	
l _{GT}	$V_D = 12V R_L = 60 \Omega$		MAX.	15	mA	
V _{GT}	$V_D = 12V R_L = 60 \Omega$		MAX.	1.5	V	
		400V		350		
	V −V + goto opon-T − 100°C	600V		300	V/µs	
	$V_D = V_{DRM}$; gate open; $T_J = 100$ °C	800V	MIN.	250		
dv/dt		1000V		100		
		400V		250		
	$V_D = V_{DRM}$; gate open; $T_J = 125$ °C	600V		225		
		800V		200		
$V_{\rm GD}$	$V_D = V_{DRM} R_L = 3.3 \text{ k}\Omega T_J = 125^{\circ}\text{C}$		MIN.	0.2	V	
I _H	$I_{T} = 200 \text{mA (initial)}$		MAX.	30	mA	
T _q	$I_T=2A$; $t_p=50\mu s$; $dv/dt=5V/\mu s$; $di/dt=-30A/\mu s$		MAX.	35	μs	
t _{gt}	$I_{G} = 2 \times I_{GT} \text{ PW} = 15 \mu \text{s} I_{T} = 16 \text{A}$		TYP.	2	μs	

Note: xx = voltage x = package

Static Characteristics

Symbol	Test Conditions					Value	Unit
V _{TM}		I _T = 16A; 1	t _p = 380 μs		MAX.	1.6	V
		T _J = 25°C		400 - 600V		5	
	SXXU8XYY	Sxx08xyy	T _J = 110°C	400 - 600V		250	
	I_{DRM}/I_{RRM} $V_{DRM} = V_{RRM}$	V _{RRM} Sxx08x	T _J = 25°C	400 - 800V	MAX.	10	
I _{DRM} / I _{RRM}				1000V		20	μΑ
			T 10000	400 - 800V		200	
	I _J = 100°C	$T_J = 100$ °C	1000V		3000		
			T _J = 125°C	400 - 800V		500	

Note: xx = voltage, x = package, yy = sensitivity



Symbol	Paramete	r	Value	Unit
		Sxx08RSy / Sxx08NSy	1.8	
		Sxx08LSy	3.4	
		Sxx08VSy	2.1	
D	lunction to cook (AC)	Sxx08DSy	1.5	9CAA/
$R_{_{ heta(J-C)}}$ Junction to case (Junction to case (AC)	Sxx08R / S xx08N	1.8	°CM
		Sxx08L	3.4	
		Sxx08V	2.0	
		Sxx08D	1.5	
		Sxx08RSy	40	
R _{θ(J-A)} Junction to ambient		Sxx08LSy	65	
	lunation to ambient	Sxx08VSy	85	°C/W
	Junction to amplent	Sxx08R	40	*C/VV
		Sxx08L	50	
	Sxx08V	70		

Note: xx = voltage, y = sensitivity

Figure 1: Normalized DC Gate Trigger Current vs. Junction Temperature (Sensitive SCR)

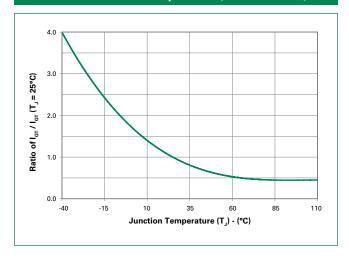


Figure 2: Normalized DC Gate Trigger Current vs. Junction Temperature (Standard SCR)

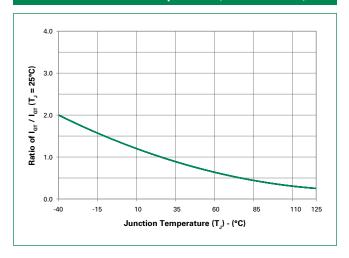




Figure 3: Normalized DC Gate Trigger Voltage vs. Junction Temperature

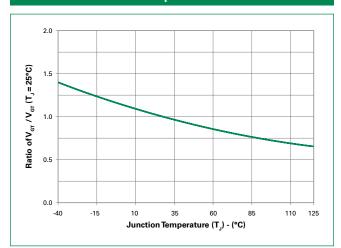


Figure 5: On-State Current
vs. On-State Voltage (Typical)

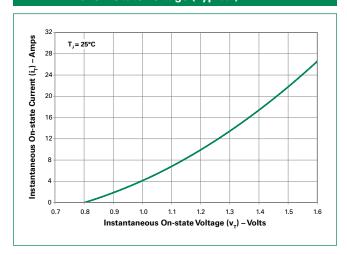
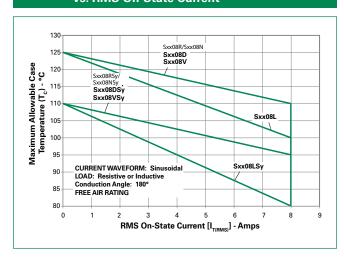


Figure 7: Maximum Allowable Case Temperature vs. RMS On-State Current



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Figure 4: Normalized DC Holding Current vs. Junction Temperature

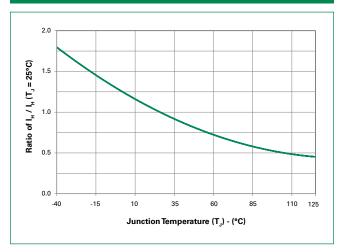


Figure 6: Power Dissipation (Typical) vs. RMS On-State Current

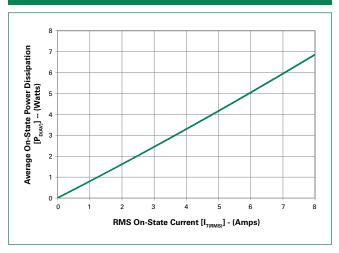


Figure 8: Maximum Allowable Case Temperature vs. Average On-State Current

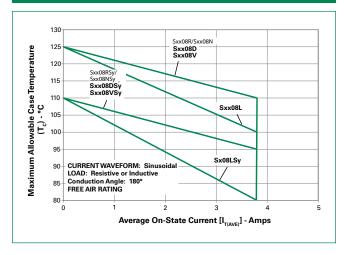
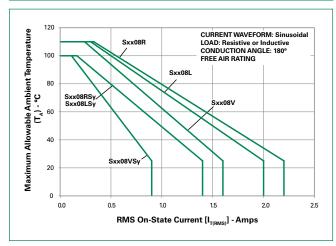




Figure 9: Maximum Allowable Ambient Temperature vs. RMS On-State Current



Note: xx = voltage, y = sensitivity

Figure 11: Peak Capacitor Discharge Current

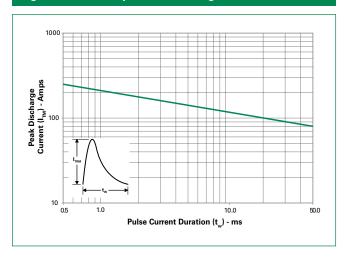


Figure 13-1: Typical DC Gate Trigger Current with R_{GK} vs. Junction Temperature for S6008xS2

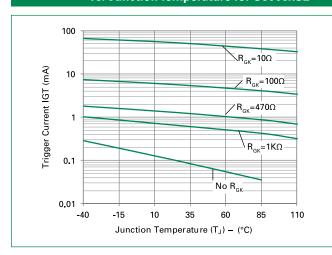


Figure 10: Maximum Allowable Ambient Temperature vs. Average On-State Current

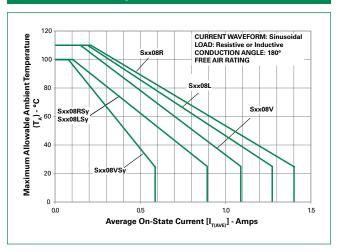


Figure 12: Peak Capacitor Discharge Current Derating

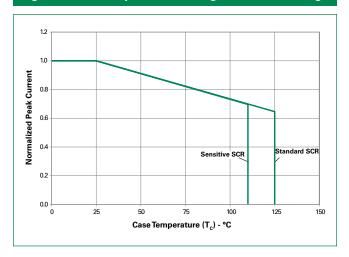


Figure 13-2: Typical DC Gate Trigger Current with R_{gk} vs. Junction Temperature for S6008xS3

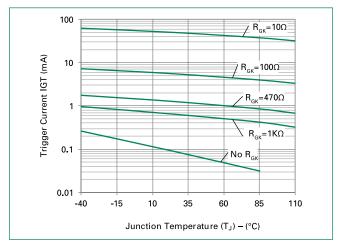




Figure 14-1: Typical DC Holding Current with R_{GK} vs. Junction Temperature for S6008xS2

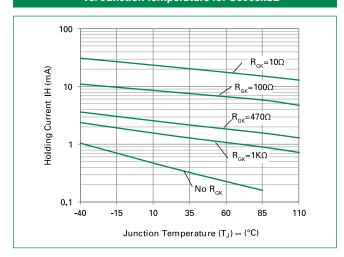


Figure 15-1: Typical Static dv/dt with R_{GK} vs. Junction Temperature for S6008xS2

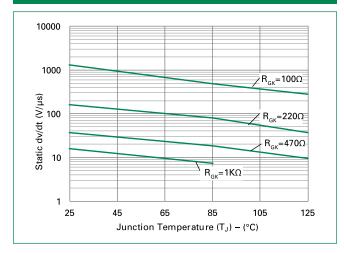
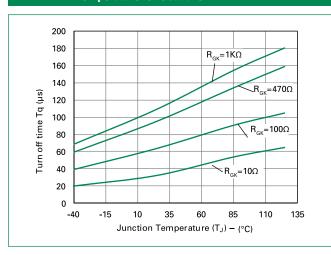


Figure 16-1: Typical turn off time with R_{GK} vs. Junction Temperature for S6008xS2



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Figure 14-1: Typical DC Holding Current with R_{GK} vs. Junction Temperature for S6008xS3

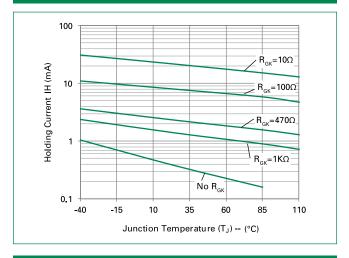


Figure 15-2: Typical Static dv/dt with R_{GK} vs. Junction Temperature for S6008xS3

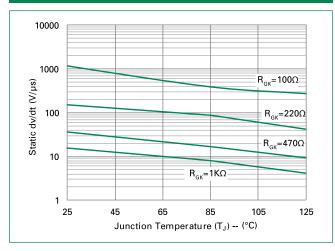
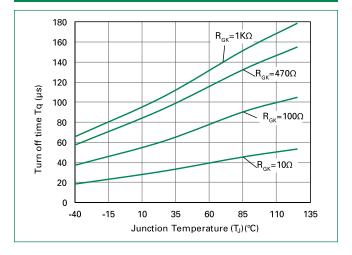


Figure 16-2: Typical DC Gate Trigger Current with R_{GK} vs. Junction Temperature for S6008xS3









SUPPLY FREQUENCY: 60 Hz Sinusoidal

LOAD: Resistive

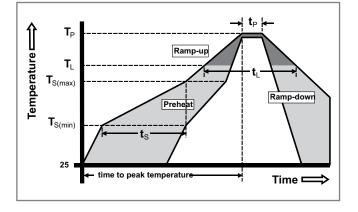
RMS On-State Current: [I $_{\rm T(RMS)}$]: Maximum Rated Value at Specified Case Temperature

Notes:

- 1. Gate control may be lost during and immediately following surge current interval.
- Overload may not be repeated until junction temperature has returned to steady-state rated value.

Soldering Parameters

Reflow Co	ndition	Pb – Free assembly
	-Temperature Min (T _{s(min)})	150°C
Pre Heat	-Temperature Max (T _{s(max)})	200°C
	-Time (min to max) (t _s)	60 – 180 secs
Average ra	amp up rate (Liquidus Temp) k	5°C/second max
T _{S(max)} to T _L - Ramp-up Rate		5°C/second max
Reflow	-Temperature (T _L) (Liquidus)	217°C
nellow	-Temperature (t _L)	60 – 150 seconds
PeakTemp	erature (T _P)	260+ ^{0/-5} °C
Time within 5°C of actual peak Temperature (t _p)		20 – 40 seconds
Ramp-down Rate		5°C/second max
Time 25°C	to peak Temperature (T _P)	8 minutes Max.
Do not exc	ceed	280°C





Physical Specifications

Terminal Finish	100% Matte Tin-plated
Body Material	UL recognized epoxy meeting flammability rating 94V-0
Lead Material	Copper Alloy

Design Considerations

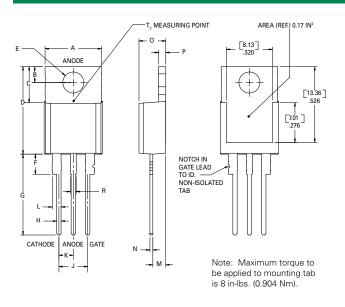
Careful selection of the correct component for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the component rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including dv/dt), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

Environmental Specifications

Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage @ 125°C for 1008 hours
Temperature Cycling	MIL-STD-750, M-1051, 100 cycles; -40°C to +150°C; 15-min dwell-time
Temperature/ Humidity	EIA / JEDEC, JESD22-A101 1008 hours; 320V - DC: 85°C; 85% rel humidity
High Temp Storage	MIL-STD-750, M-1031, 1008 hours; 150°C
Low-Temp Storage	1008 hours; -40°C
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Lead Bend	MIL-STD-750, M-2036 Cond E

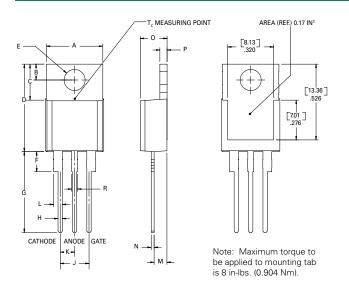


Dimensions — TO-220AB (R-Package) — Non-Isolated Mounting Tab Common with Center Lead



Dimension	Inc	hes	Millimeters		
Dimension	Min	Max	Min	Max	
А	0.380	0.420	9.65	10.67	
В	0.105	0.115	2.67	2.92	
С	0.230	0.250	5.84	6.35	
D	0.590	0.620	14.99	15.75	
Е	0.142	0.147	3.61	3.73	
F	0.110	0.130	2.79	3.30	
G	0.540	0.575	13.72	14.61	
Н	0.025	0.035	0.64	0.89	
J	0.195	0.205	4.95	5.21	
K	0.095	0.105	2.41	2.67	
L	0.060	0.075	1.52	1.91	
М	0.085	0.095	2.16	2.41	
N	0.018	0.024	0.46	0.61	
0	0.178	0.188	4.52	4.78	
Р	0.045	0.060	1.14	1.52	
R	0.038	0.048	0.97	1.22	

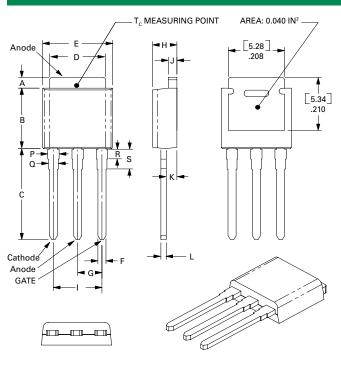
Dimensions — TO-220AB (L-Package) — Isolated Mounting Tab



Dimension	Inc	hes	Millimeters		
Difficusion	Min	Max	Min	Max	
А	0.380	0.420	9.65	10.67	
В	0.105	0.115	2.67	2.92	
С	0.230	0.250	5.84	6.35	
D	0.590	0.620	14.99	15.75	
Е	0.142	0.147	3.61	3.73	
F	0.110	0.130	2.79	3.30	
G	0.540	0.575	13.72	14.61	
Н	0.025	0.035	0.64	0.89	
J	0.195	0.205	4.95	5.21	
K	0.095	0.105	2.41	2.67	
L	0.060	0.075	1.52	1.91	
М	0.085	0.095	2.16	2.41	
N	0.018	0.024	0.46	0.61	
0	0.178	0.188	4.52	4.78	
Р	0.045	0.060	1.14	1.52	
R	0.038	0.048	0.97	1.22	

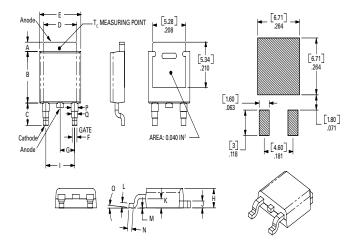


Dimensions — TO-251AA (V/I-Package) — V/I-PAK Through Hole



Discouries		Inches		Millimeters		
Dimension	Min	Тур	Max	Min	Тур	Max
А	0.037	0.040	0.043	0.94	1.01	1.09
В	0.235	0.242	0.245	5.97	6.15	6.22
С	0.350	0.361	0.375	8.89	9.18	9.53
D	0.205	0.208	0.213	5.21	5.29	5.41
Е	0.255	0.262	0.265	6.48	6.66	6.73
F	0.027	0.031	0.033	0.69	0.80	0.84
G	0.087	0.090	0.093	2.21	2.28	2.36
Н	0.085	0.092	0.095	2.16	2.34	2.41
I	0.176	0.180	0.184	4.47	4.57	4.67
J	0.018	0.020	0.023	0.46	0.51	0.58
K	0.035	0.037	0.039	0.90	0.95	1.00
L	0.018	0.020	0.023	0.46	0.52	0.58
Р	0.042	0.047	0.052	1.06	1.20	1.32
Q	0.034	0.039	0.044	0.86	1.00	1.11
R	0.034	0.039	0.044	0.86	1.00	1.11
S	0.074	0.079	0.084	1.86	2.00	2.11

Dimensions - TO-252AA (D-Package) - D-PAK Surface Mount



Dimension		Inches		Millimeters		
Dimension	Min	Тур	Max	Min	Тур	Max
А	0.037	0.040	0.043	0.94	1.01	1.09
В	0.235	0.243	0.245	5.97	6.16	6.22
С	0.106	0.108	0.113	2.69	2.74	2.87
D	0.205	0.208	0.213	5.21	5.29	5.41
E	0.255	0.262	0.265	6.48	6.65	6.73
F	0.027	0.031	0.033	0.69	0.80	0.84
G	0.087	0.090	0.093	2.21	2.28	2.36
Н	0.085	0.092	0.095	2.16	2.33	2.41
I	0.176	0.179	0.184	4.47	4.55	4.67
J	0.018	0.020	0.023	0.46	0.51	0.58
K	0.035	0.037	0.039	0.90	0.95	1.00
L	0.018	0.020	0.023	0.46	0.51	0.58
М	0.000	0.000	0.004	0.00	0.00	0.10
N	0.021	0.026	0.027	0.53	0.67	0.69
0	0°	0°	5°	0°	0°	5°
Р	0.042	0.047	0.052	1.06	1.20	1.32
Q	0.034	0.039	0.044	0.86	1.00	1.11

Thyristors 8 Amp Sensitive & Standard SCRs

Product Selector							
Part Number	Voltage				Gate Sensitivity	Туре	Package
	400V	600V	800V	1000V	Guto Conontrity	1,750	rackago
Sxx08RS2	X	X			0.2mA	Sensitive SCR	TO-220R
Sxx08LS2	X	X			0.2mA	Sensitive SCR	TO-220L
Sxx08VS2	X	X			0.2mA	Sensitive SCR	TO-251
Sxx08DS2	X	X			0.2mA	Sensitive SCR	TO-252
Sxx08RS3	X	X			0.5mA	Sensitive SCR	TO-220R
Sxx08LS3	X	X			0.5mA	Sensitive SCR	TO-220L
Sxx08VS3	X	X			0.5mA	Sensitive SCR	TO-251
Sxx08DS3	X	X			0.5mA	Sensitive SCR	TO-252
Sxx08R	X	X	X	X	15mA	Standard SCR	TO-220R
Sxx08L	X	X	X	X	15mA	Standard SCR	TO-220L
Sxx08V	X	X	X	X	15mA	Standard SCR	TO-251
Sxx08D	X	Х	X	X	15mA	Standard SCR	TO-252
Sxx08NS2	Х	Х			0.2mA	Sensitive SCR	TO-263
Sxx08NS3	X	X			0.5mA	Sensitive SCR	TO-263
Sxx08N	Х	Х	X	X	15mA	Standard SCR	TO-263
Sxx08DS1		X			50μΑ	Sensitive SCR	TO-252

100μΑ

Sensitive SCR

TO-252

Sxx08DS4

Note: xx = Voltage/10

Packing Options

Part Number	Marking	Weight	Packing Mode	Base Quantity
Sxx08L/RyyTP	Sxx08L/Ryy	2.2 g	Tube	500 (50 per tube)
Sxx08DyyTP	Sxx08Dyy	0.3 g	Tube	750 (75 per tube)
Sxx08DyyRP	Sxx08Dyy	0.3 g	Embossed Carrier	2500
Sxx08VyyTP	Sxx08Vyy	0.4 g	Tube	750 (75 per tube)
Sxx08L/RTP	Sxx08L/R	2.2 g	Tube	500 (50 per tube)
Sxx08DTP	Sxx08D	0.3 g	Tube	750 (75 per tube)
Sxx08DRP	Sxx08D	0.3 g	Embossed Carrier	2500
Sxx08NyyTP	Sxx08Nyy	1.6g	Tube	500 (50 per tube)
Sxx08NyyRP	Sxx08Nyy	1.6g	Embossed Carrier	500
Sxx08VyyNTP	Sxx08N	1.6g	Tube	500 (50 per tube)
Sxx08NTP	Sxx08N	1.6g	Embossed Carrier	500
Sxx08NRP	Sxx08V	0.4 g	Tube	750 (75 per tube)

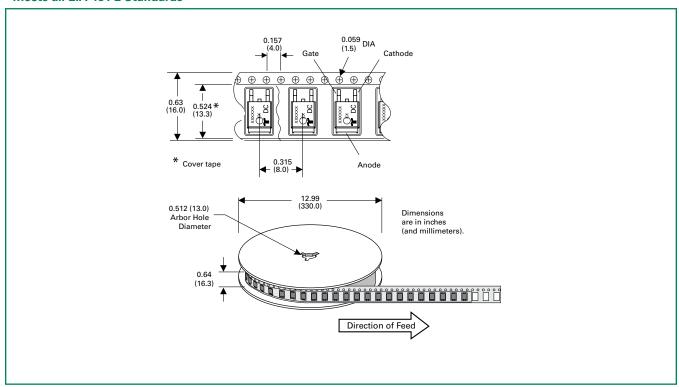
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Note: xx = Voltage/10; yy = Sensitivity

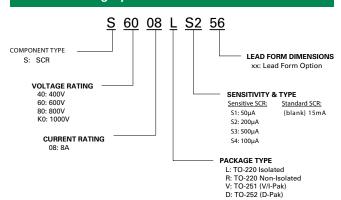


TO-252 Embossed Carrier Reel Pack (RP) Specifications

Meets all EIA-481-2 Standards

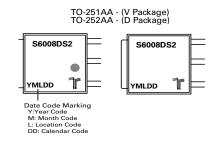


Part Numbering System

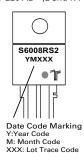


N: TO-263 (D2PAK)

Part Marking System



TO-263 AA (N Package) TO-220 AB - (L and R Package)



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